2SA1617

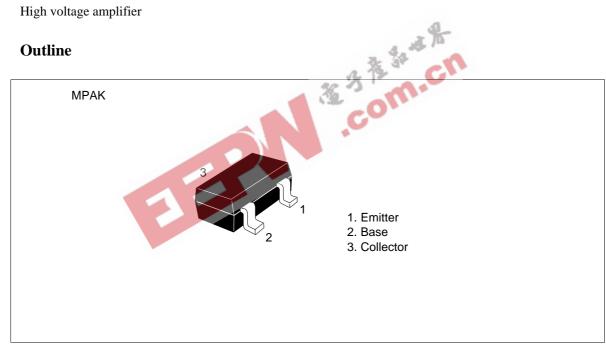
Silicon PNP Epitaxial

HITACHI

Application

High voltage amplifier

Outline





2SA1617

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	– 55	V
Collector to emitter voltage	V_{CEO}	– 50	V
Emitter to base voltage	V_{EBO}	- 5	V
Collector current	I _c	-100	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

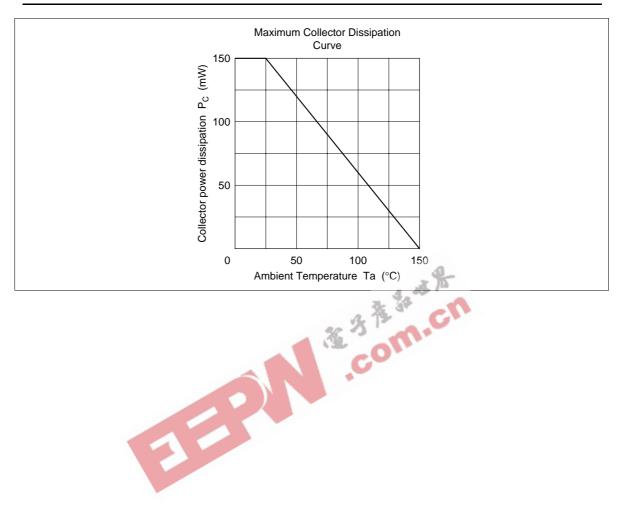
Electrical Characteristics ($Ta = 25^{\circ}C$)				A AT The		
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-55	3	25	V	$I_{c} = -10 \mu\text{A}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	7-1	.00	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 5	_	_	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	СВО	_	_	-0.5	μΑ	$V_{CB} = -30 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	-0.5	μΑ	$V_{EB} = -2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	100	_	320		$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.2	V	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	-0.8	V	$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}$

Note: 1. The 2SA1617 is grouped by $h_{\rm FE}$ as follows.

Grade	В	С
Mark	VIB	VIC
h _{FE}	100 to 200	160 to 320

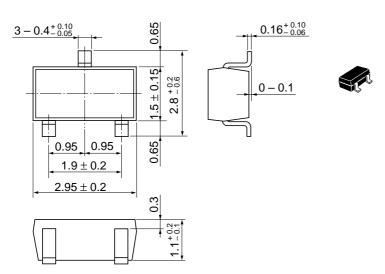
See charcteristic curves of 2SA1031

2SA1617





Unit: mm



Hitachi Code	MPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.011 a

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